

650V N-CHANNEL ENHANCEMENT MODE MOSFET

MAIN CHARACTERISTICS

I_D	2A
V_{DSS}	650V
$R_{DS(on)-typ}(@V_{GS}=10V)$	$<4.8\Omega$ (Type: 4 Ω)

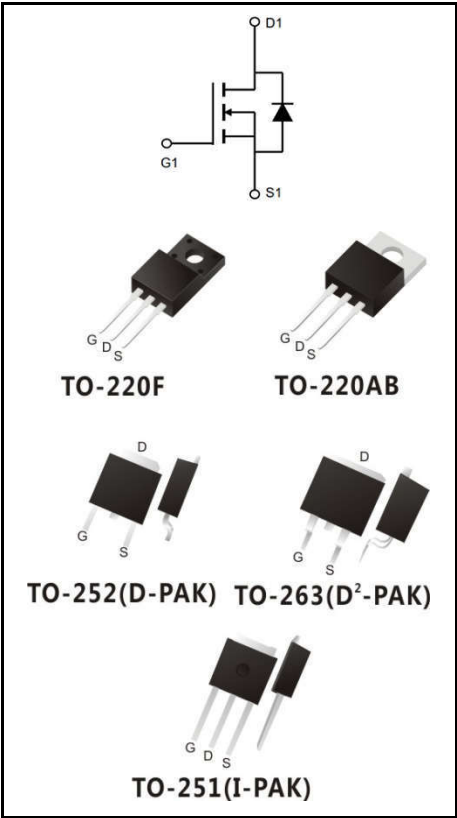


Features

- ◆Fast Switching
- ◆Low ON Resistance
- ◆Low Gate Charge
- ◆100% Single Pulse avalanche energy Test
- ◆LeadfreeincomplywithEUroHS2011/65/EUdirectives

Mechanical Data

- ◆Case: Molded plastic
- ◆Mounting Position: Any
- ◆Molded Plastic: UL Flammability Classification Rating 94V-0
- ◆Solder bath temperature275℃maximum,10s per JESD22-106



Product Specification Classification

Part Number	Package	Marking	Pack
YFW2N65AT	TO-220AB	YFW 2N65AT XXXXX	50PCS/Tube
YFW2N65AF	TO-220F(0.5mm)	YFW 2N65AF XXXXX	50PCS/Tube
YFW2N65AS	TO-263	YFW 2N65AS XXXXX	50PCS/Tube
YFW2N65AS-R	TO-263	YFW 2N65AS XXXXX	800PCS/Tape
YFW2N65AMJ	TO-251	YFW 2N65AMJ XXXXX	4000PCS/Tape
YFW2N65AD	TO-252	YFW 2N65AD XXXXX	2500PCS/Tape

Maximum Ratings at Tc=25°C unless otherwise specified

Characteristics	Symbols	Value		Units
		220F	220/251/252	
Drain-Source Voltage	V_{DS}	650		V
Gate-Source Voltage	V_{GS}	±30		V
Continue Drain Current -Continuous	I_D	2		A
Pulsed Drain Current (Note1)	I_{DM}	8		A
Power Dissipation	P_D	25	35	W
Single Pulse Avalanche Energy (Note1)	E_{AS}	65		mJ
Operating Temperature Range	T_J	150		°C
Storage Temperature Range	T_{STG}	-55 to +150		°C
Thermal Resistance, Junction to Case	$R_{\theta JC}$	5.24	3.57	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	62.5	62.5	°C/W

Maximum Ratings at Tc=25°C unless otherwise specified

Characteristics	Test Condition	Symbols	Min	Typ	Max	Units
Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	BV_{DSS}	650	682	-	V
Drain-Source Leakage Current	$V_{DS} = 650\text{ V}, V_{GS} = 0\text{ V}$	I_{DSS}	-	-	1	uA
Gate Leakage Current	$V_{GS} = \pm 30\text{ V}, V_{DS} = 0\text{ V}$	I_{GSS}	-	-	±100	nA
Gate-Source Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	$V_{GS(th)}$	2	-	4	V
Drain-Source On-State Resistance	$V_{GS} = 10\text{ V}, I_D = 1\text{ A}$	$R_{DS(on)}$	-	4.0	4.8	Ω
Forward Transconductance	$V_{DS} = 15\text{ V}, I_D = 2\text{ A}$	g_{fs}	-	2.5	-	S
Input Capacitance	$V_{GS} = 0\text{ V},$ $V_{DS} = 2\text{ V},$ $f = 200\text{ KHz}$	C_{iss}	-	415	-	pF
Output Capacitance		C_{oss}	-	32	-	
Reverse Transfer Capacitance		C_{rss}	-	6	-	
Turn-on Delay Time	$I_D = 2\text{ A},$ $V_{DD} = 325\text{ V},$ $R_G = 10\text{ }\Omega$	$td(ON)$	-	8	-	nS
Rise Time(Note2)		tr	-	6	-	
Turn-Off Delay Time(Note2)		$td(OFF)$	-	30	-	
Fall Time(Note2)		tf	-	11	-	
Total Gate Charge(Note2)	$I_D = 2\text{ A},$ $V_{DD} = 520\text{ V},$ $V_{GS} = 10\text{ V}$	Q_G	-	10.8	-	nC
Gate to Source Charge(Note2)		Q_{GS}	-	1.5	-	
Gate to Drain Charge(Note2)		Q_{GD}	-	4	-	

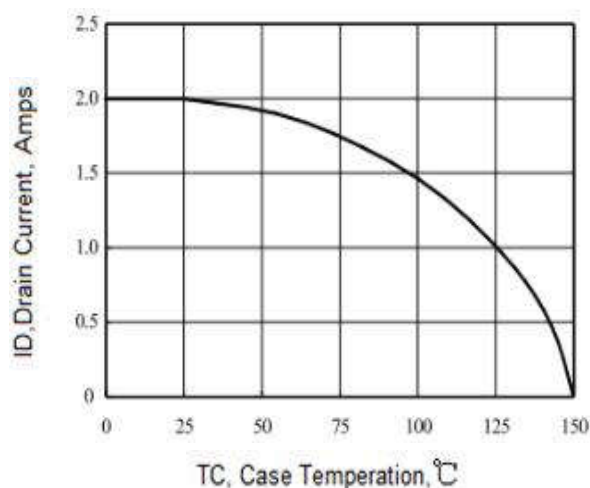
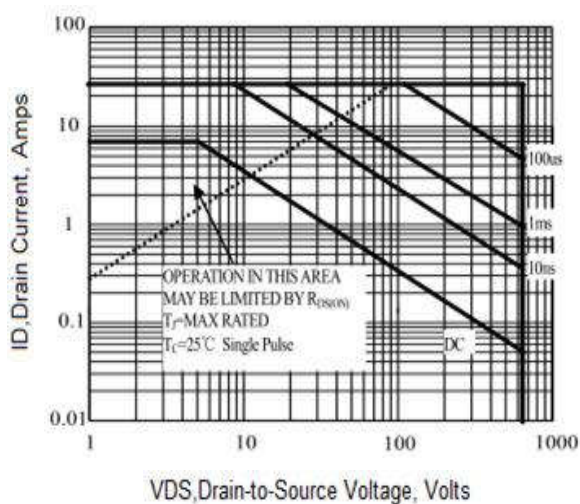
Source-Drain Diode Characteristics at Ta=25°C unless otherwise specified

Characteristics	Test Condition	Symbols	Min	Typ	Max	Units
Maximum Body-Diode Pulsed Current		I_S	-	-	2	A
Maximum Body-Diode Pulsed Current(Note2)		I_{SM}	-	-	8	A
Drain-Source Diode Forward Voltage	I_{SD} = 2 A	V_{SD}	-	-	1.4	V
Reverse Recovery Time(Note2)	I_{SD} = 2 A, V_{GS} = 0 V, dI_F / dt = 100 A/μs	trr	-	430	-	nS
Reverse Recovery Charge(Note2)		Qrr	-	1.1	-	uC

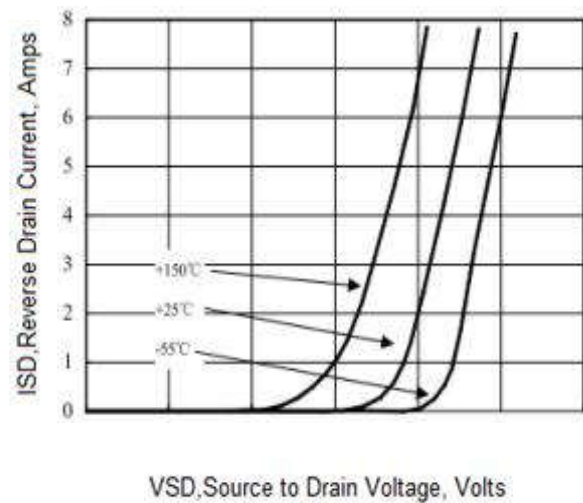
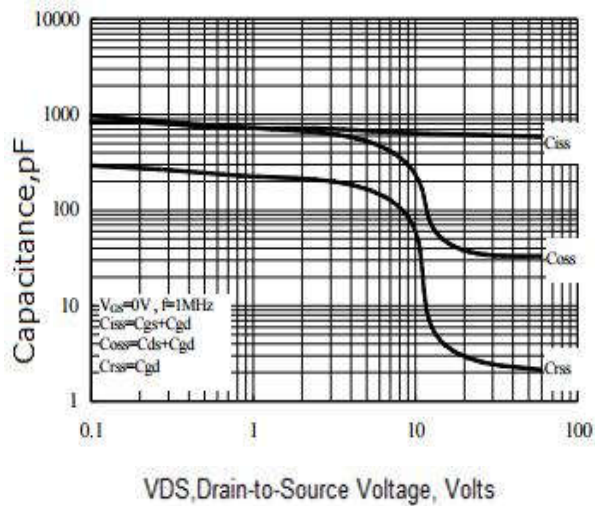
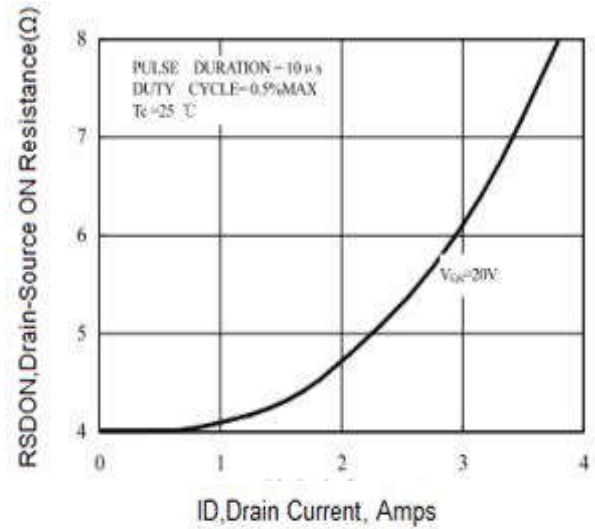
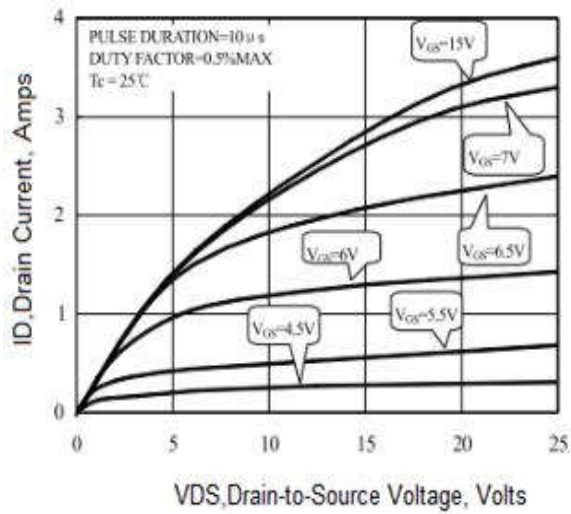
Note:

1. Pulse test: 300 μs pulse width, 2 % duty cycle
2. Pulse test: 300 μs pulse width, 2 % duty cycle

Ratings and Characteristic Curves

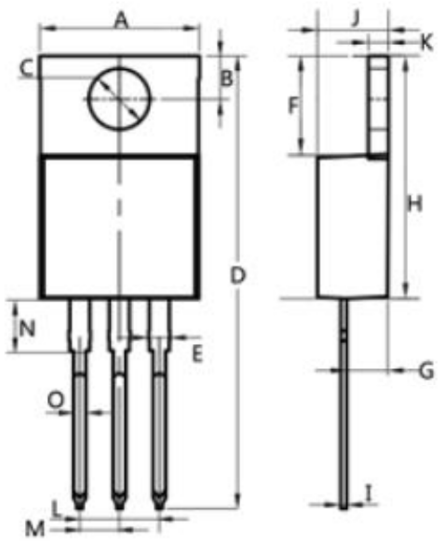


Ratings and Characteristic Curves

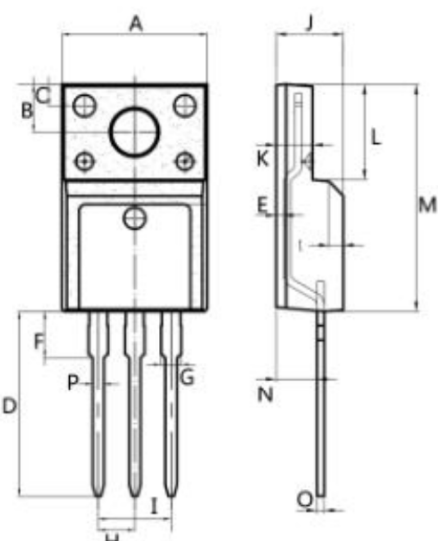


Package Outline Dimensions Millimeters

TO-220AB

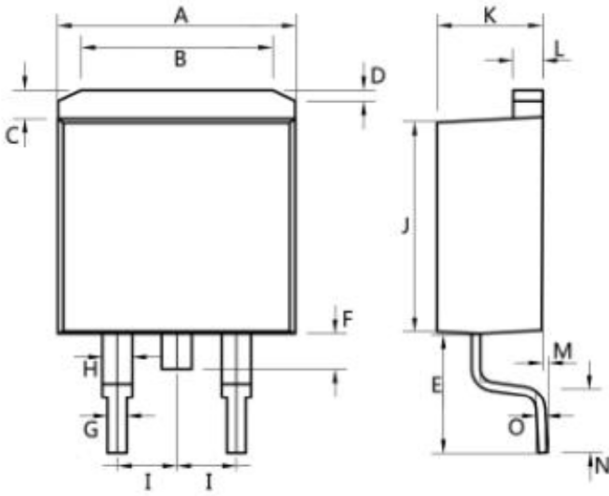
	Dim.	Min.	Max.
	A	10.15	10.35
	B	2.65	2.95
	C	3.70	3.90
	D	28.5	29.5
	E	1.30	1.25
	F	6.35	6.55
	G	2.9	3.3
	H	15.0	16.0
	I	0.38	0.22
	J	2.25	2.55
	K	1.25	1.35
	L	Typ 5.08	
	M	Typ 2.52	
	N	3.1	3.3
	O	0.76	0.82
All Dimensions in millimeter			

TO-220F

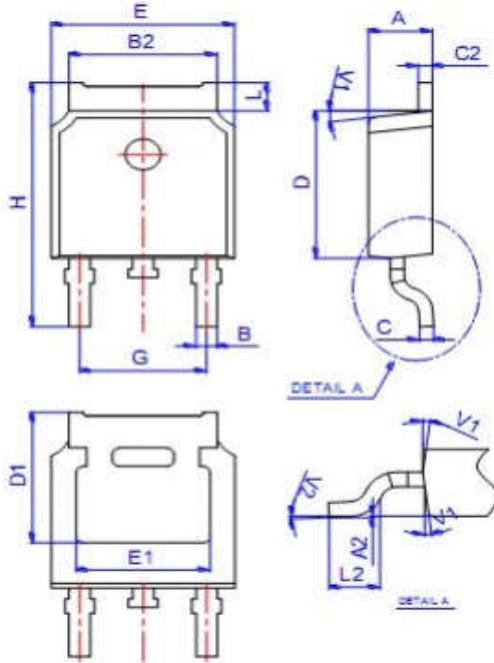
	Dim.	Min.	Max.
	A	9.95	10.25
	B	2.95	3.25
	C	1.25	1.25
	D	12.95	13.25
	E	0.50	0.65
	F	3.1	3.3
	G	1.30	1.25
	H	Typ 2.52	
	I	Typ 5.08	
	J	2.60	2.75
	K	2.50	2.65
	L	6.35	6.55
	M	15.2	16.0
	N	2.75	3.05
	O	0.28	0.52
	P	0.76	0.82
All Dimensions in millimeter			

Package Outline Dimensions Millimeters

TO-263

	Dim.	Min.	Max.
	A	10.1	10.2
	B	7.2	7.6
	C	1.3	1.5
	D	0.55	0.75
	E	5.0	6.0
	F	1.2	1.6
	G	0.78	0.86
	H	1.2	1.3
	I	Typ2.52	
	J	8.2	8.6
	K	2.25	2.55
	L	1.25	1.35
	M	0.02	0.1
	N	2.2	2.8
	O	0.36	0.20
All Dimensions in millimeter			

TO-252

	Dim.	Min.	Typ.	Max.
	A	2.10	-	2.50
	A2	0	-	0.10
	B	0.66	-	0.86
	B2	5.18	-	5.48
	C	0.40	-	0.60
	C2	0.44	-	0.58
	D	5.90	-	6.30
	D1	5.30REF		
	E	6.40	-	6.80
	E1	4.63	-	-
	G	4.47	-	4.67
	H	9.50	-	10.70
	L	1.09	-	1.21
	L2	1.35	-	1.65
	V1	-	7°	-
	V2	0°	-	6°
All Dimensions in millimeter				

Package Outline Dimensions Millimeters

TO-251

	Dim.	Min.	Max.
	A	2.2	2.2
	A2	0.95	1.15
	A3	0.25	0.65
	b	0.65	0.85
	c	0.25	0.55
	D	6.25	6.75
	D2	5.2	5.2
	E	5.8	6
	E2	0.95	1.25
	e	Typ 2.3	
	e1	Typ 2.6	
	L	2	2.2
	L1	1.2	1.5
All Dimensions in millimeter			